Adding a New Dimension to Physical Design

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Outline

- What is 3D about?
- Why 3D?
- 3D-specific challenges
- 3D analysis and optimization

Planning a city: Land usage

[Somewhere in the American midwest; pop. density typically about 20 persons/km²]



[Minneapolis, p.d. = $2,700/\text{km}^2$] [SF= $6,688/\text{km}^2$]

$$[SF = 6.688/km^2]$$

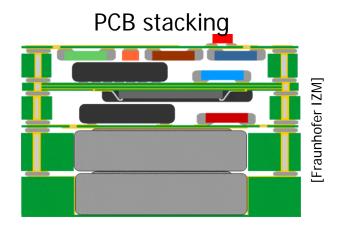
[New York=10,600/km²]







Types of 3D circuits



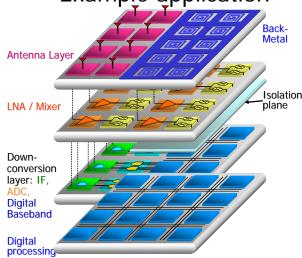
Memory – vertical TFTs



Wafer stacking



Example application



Example of a commercial application

STMicroelectronics CMOS camera



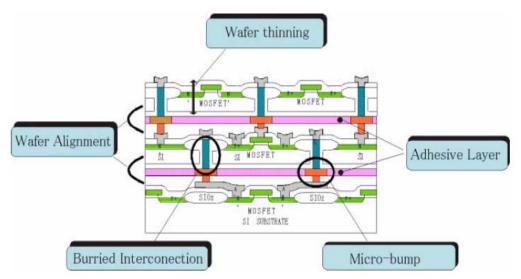


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depending on the production period and quantities. ST's VD6725 single-

chip camera sensor is available in two package options, as a COB (Chip On Board) die or in the TSV wafer-level package. The sensor fits in phone camera modules smaller than 6 x 6 x 3.8 mm thanks to its 1.75-micron pixel design and ST's advanced sensor architecture.

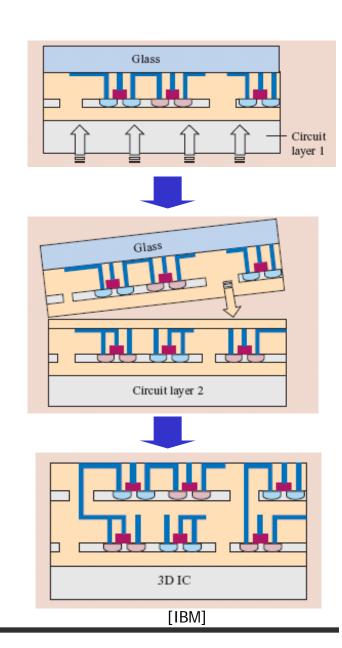
Example 3D processes



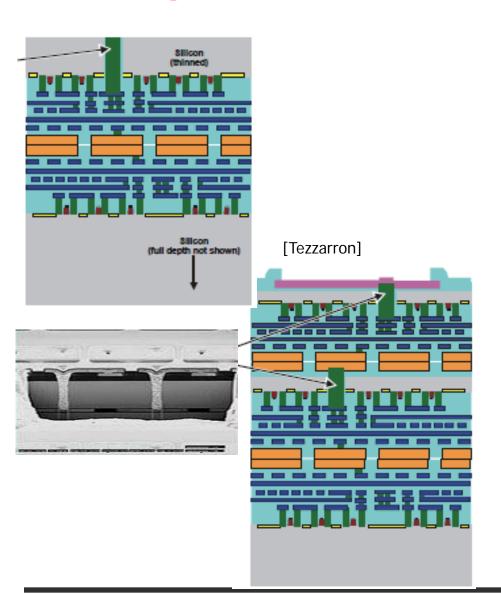
[Koyanagi, Tohoku U./Zycube]



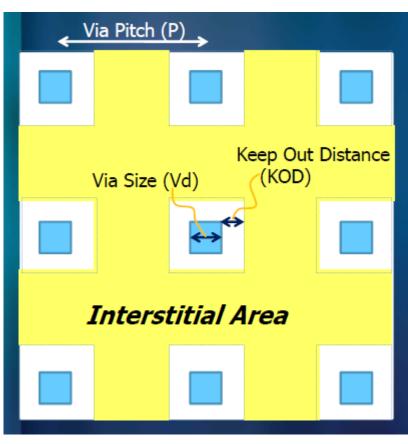
[Hedler, Qimonda]



Through-silicon vias (TSVs)

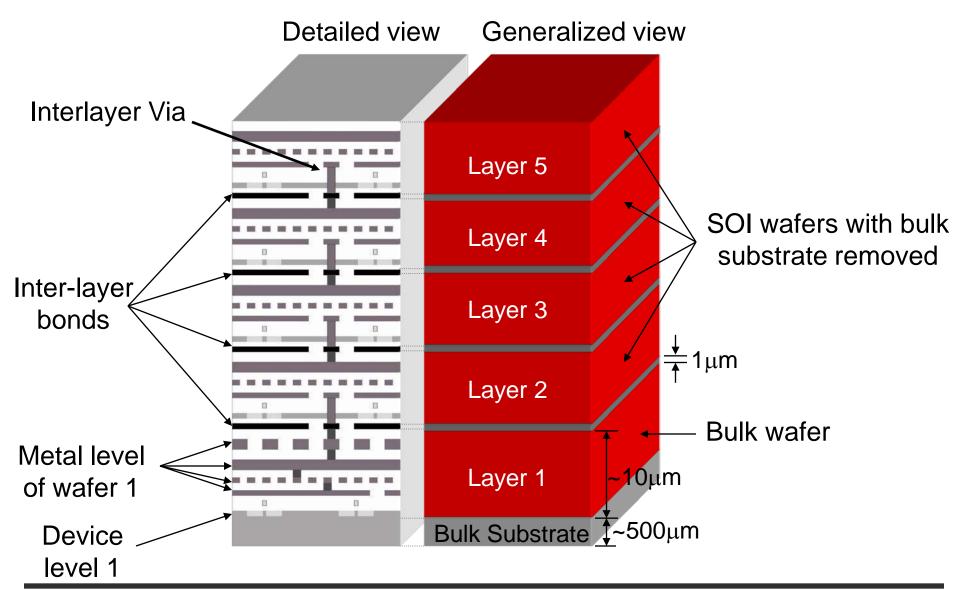


Keep-out distance



[Nowak, Qualcomm]

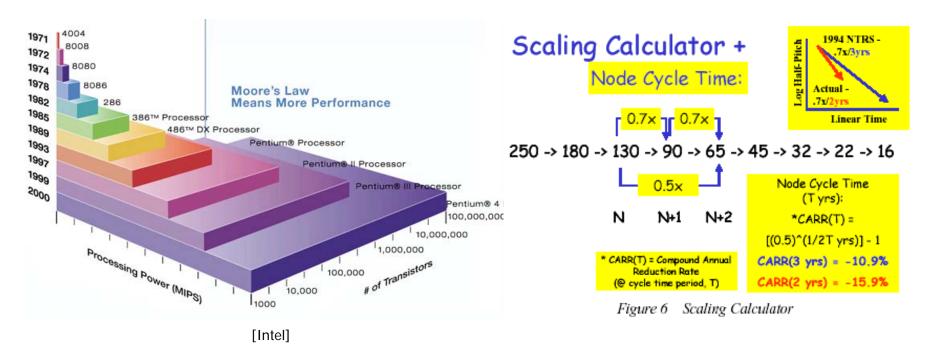
Schematic of a 3D IC



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Another "dimension" to scaling

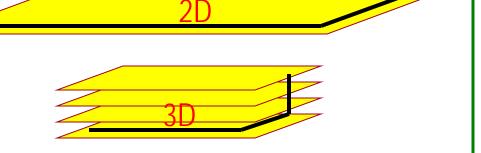


3D provides an alternative avenue towards increasing system sizes

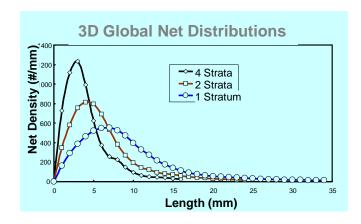
Orthogonal to device scaling

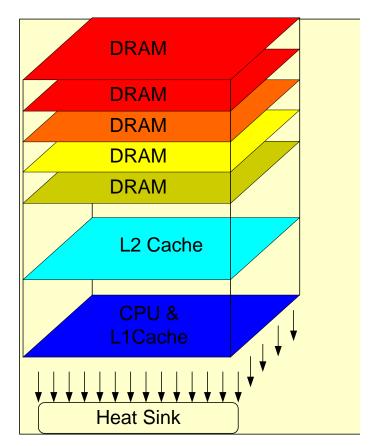
3D Interconnects

Reduced wire lengths



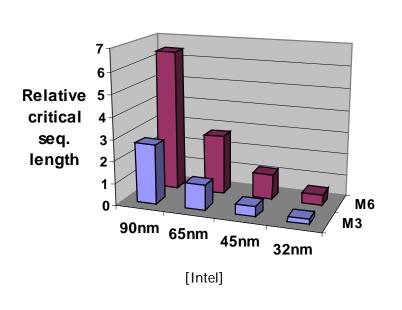
- Theoretically
 - For an $L \times L$ 2D chip, max wire length reduces from 2L to $\frac{2L}{\sqrt{n}}$

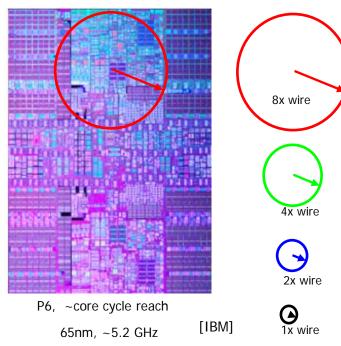




Why are shorter wires good?

Sequential critical length ("cycle reach") trends

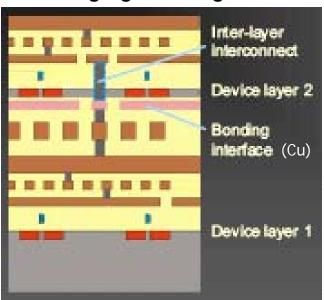




 Critical interbuffer length also shrinking (i.e., buffer count increasing)

Other benefits

- Improved isolation in 3D
 - Critical for analog/RF ckts
 - Lower digital/mixed-signal noise
 - Shielding is possible either using metal layers, or by leveraging bonding material



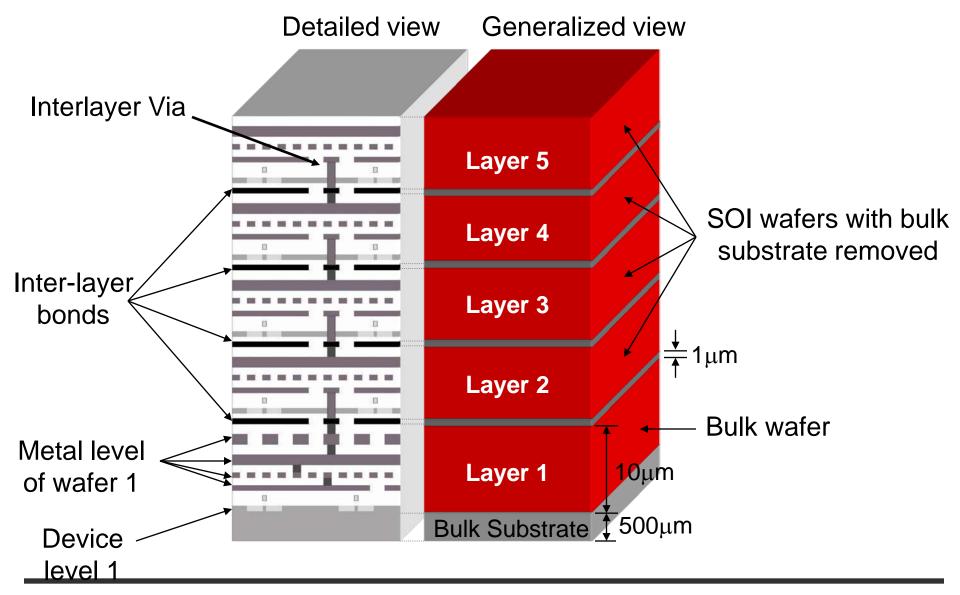
[Das *et al.*, ISPD04]

- Heterogeneous integration
 - Different layers can be made of different materials
 - Can integrate, for example
 - CMOS
 - GaAs
 - Optical elements (VCSELs)
 - MEMS/NEMS
 - Exotic cooling technologies (micropumps, piezoelectric devices, microrefrigerators)

Outline

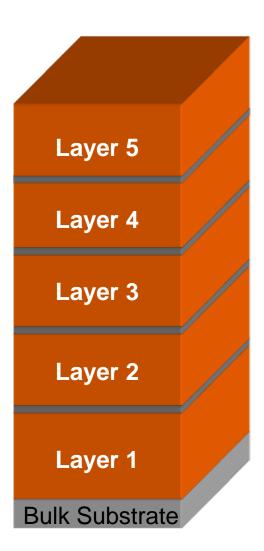
- What is 3D about?
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Geometrical challenges



Thermal challenges

- Each layer generates heat
- Heat sink at the end(s)
- Simple analysis
 - Power(3D)/Power(2D) = m
 - *m* = # layers
 - Let R_{sink} = thermal resistance of heat sink
 - $T = Power \times R_{sink}$
 - *m* times worse for 3D!
- And this does not account for
 - Increased effective R_{sink}
 - Leakage power effects, T-leakage feedback
- Thermal bottleneck: a major problem for 3D



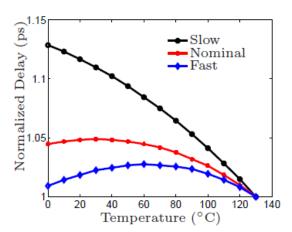
Thermal impact on circuit performance

- Gate delays change with T
 - Mobility goes down

$$\mu(T) = \mu(T_0) \left(\frac{T}{T_0}\right)^{-m}$$
 – V_{th} goes down

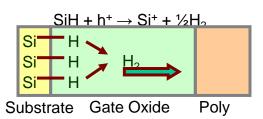
$$V_{\rm th}(T) = V_{th}(T_0) - \kappa(T - T_0)$$

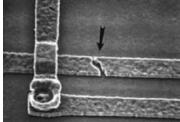
- Which effect wins?
- Positive, negative, mixed T dependency



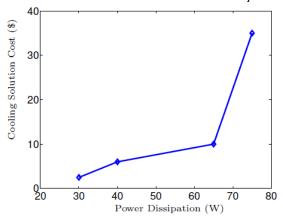
The same circuit at various process corners

- Wire delays change with T
- Leakage increases with T
- Reliability degrades with T
 - NBTI, electromigration





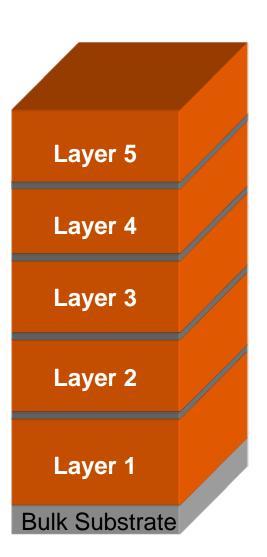
Can use better heat sinks, but...



Heat sink cost vs. Power

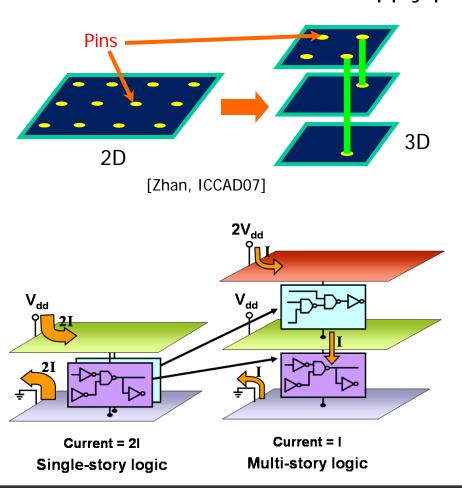
Power delivery challenges

- Each layer draws current from the power grid
- Power pins at the extreme end tier(s)
- Simple analysis
 - Current(3D)/Current(2D) = m
 - *m* = # layers
 - Let R_{grid} = resistance of power grid
 - $V_{drop} = Current \times R_{grid}$
 - *m* times worse for 3D!
- And this does not account for
 - Increased effective R_{grid}
 - Leakage power effects, increased current due to T-leakage feedback
- Power bottleneck: a major problem for 3D

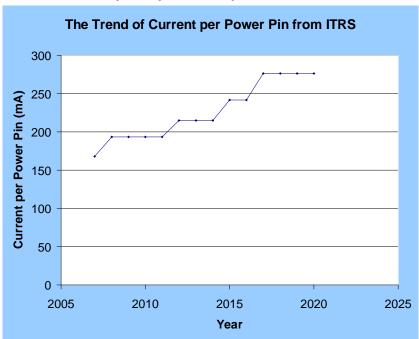


Power supply integrity in 3D

 Greater challenge in 3D due to via resistance, limited number of supply pins

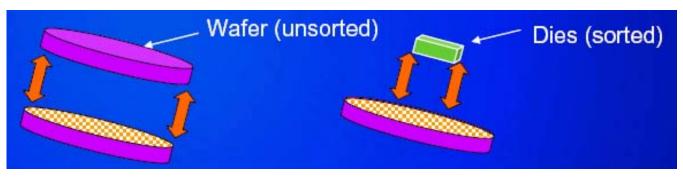


Current per power pin (2D) – ITRS



Yield/test challenges

- Yield due to spot defects reduces exponentially with area
 - Smaller areas imply better yield
 - Stack together smaller die; yield improves!
 - (Note that stacking wafers together does not help!)



[Mak, Intel]

- Problem
 - Need to have known-good die (KGD)
 - Must test die prior to 3D assembly
- Testing thinned die is hard: mechanically too weak for probe pressure!
- Can test die prior to thinning but then, connections to other layers are untested!

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Thermal analysis

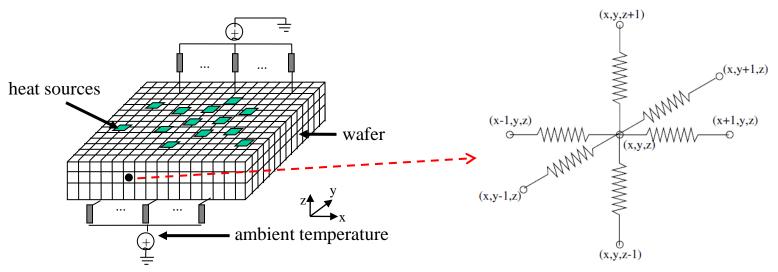
- Heat generation
 - Switching gates/blocks act as heat sources
 - Time constants for heat of the order of ms or more
- Thermal equation: partial differential equation

$$K_{x} \frac{\partial^{2} T}{\partial x^{2}} + K_{y} \frac{\partial^{2} T}{\partial y^{2}} + K_{z} \frac{\partial^{2} T}{\partial z^{2}} + Q(x, y, z) = 0$$

- Boundary conditions corresponding to the ambient, heat sink, etc.
- Self-consistency
 - Power = f(T)
 - T = g(Power)

Thermal solution techniques

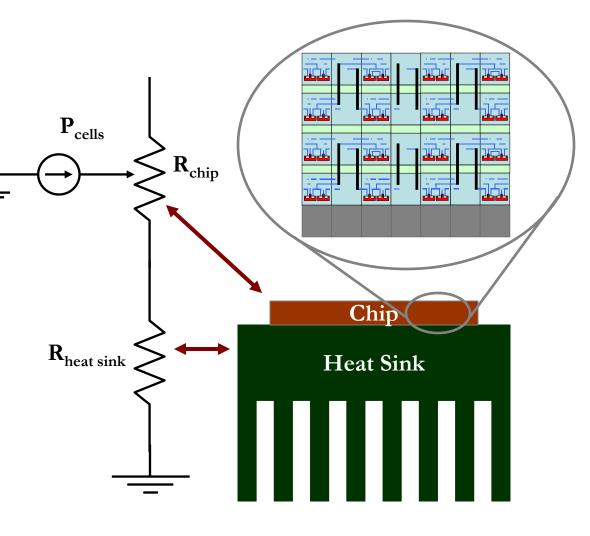
- Numerical: solve large, sparse systems of linear equations
 - Finite difference method: thermal electrical equivalence
 - System structure is similar to power grids (good!)



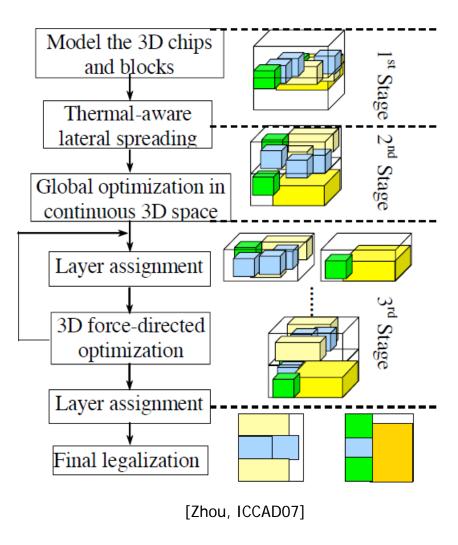
- Current sources ↔ power, voltage ↔ temperature
- Finite element method
- Semi-analytical
 - Green functions (fast, appropriate for early analysis)

Thermal optimization

- Minimize power usage
- Rearrange heat sources
- Improved thermal conduits
- Improved heat sinking

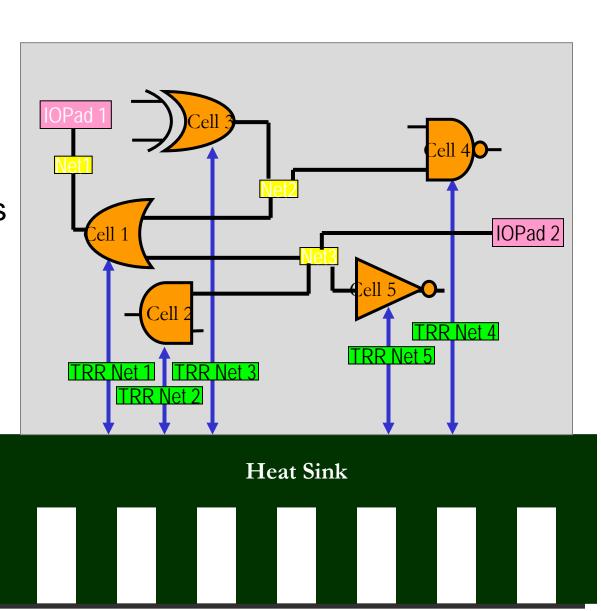


3D floorplanning

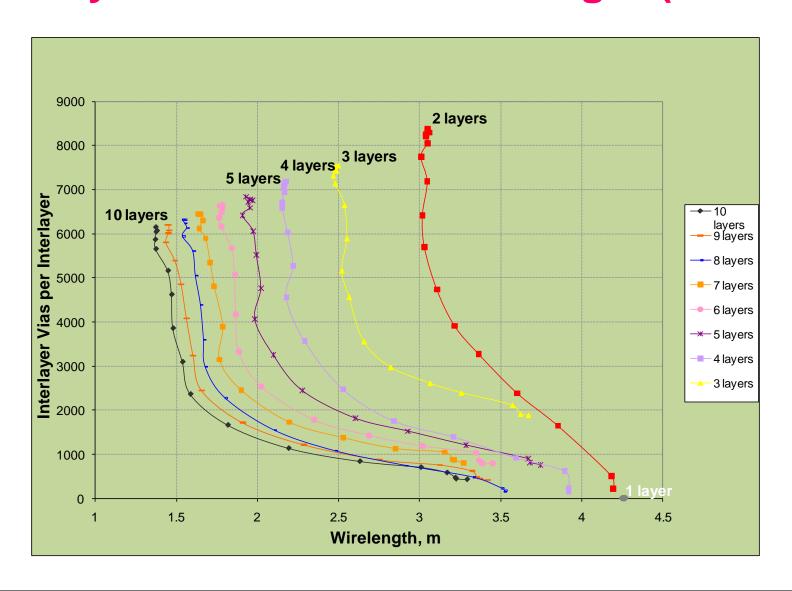


3D placement

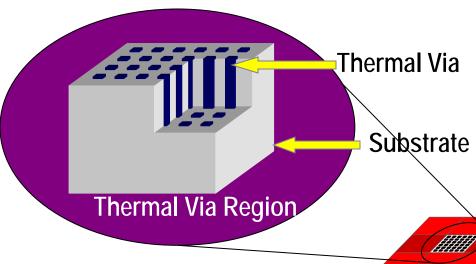
- Incorporate thermal issues
- Force-directed vs.
 partitioning methods



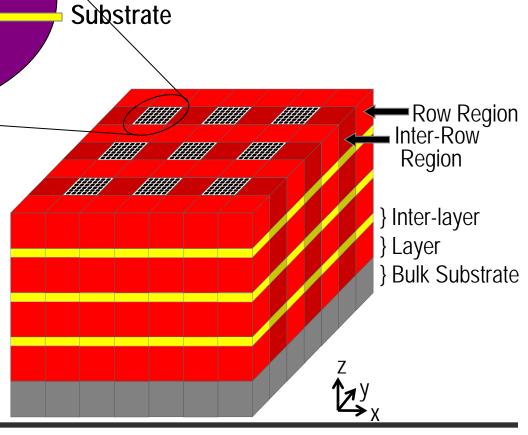
Interlayer via count vs. wirelength (ibm01)



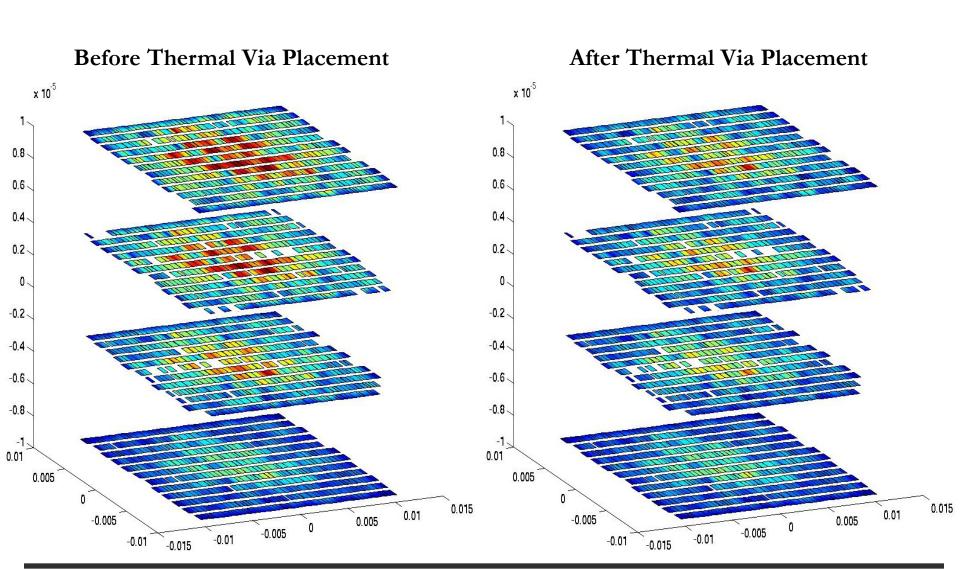
Thermal vias



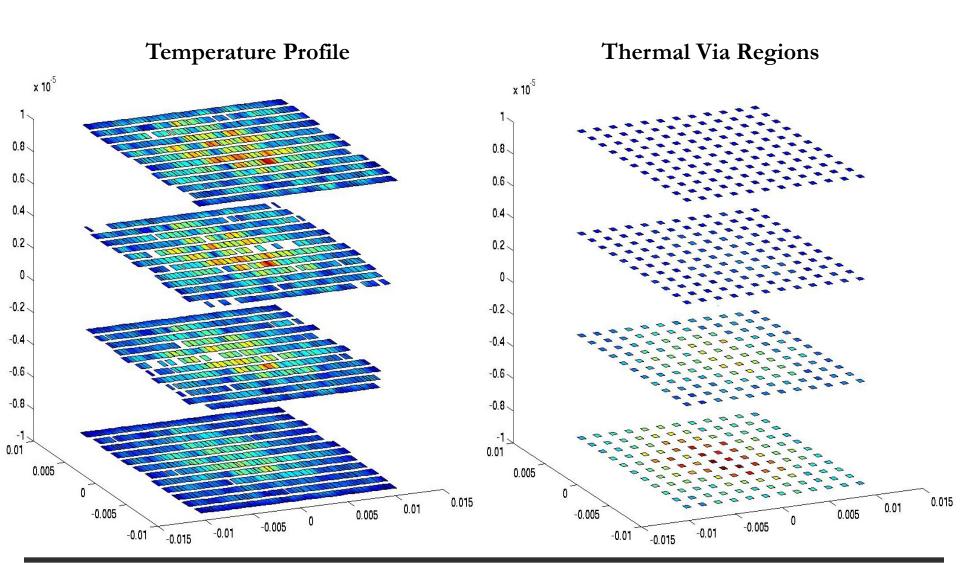
- Thermal vias
 - Electrically isolated vias
 - Used for heat conduction
- Thermal via regions
 - Contains thermal vias
 - Predictable obstacle for routing
 - Variable density of thermal vias



Temperature profile



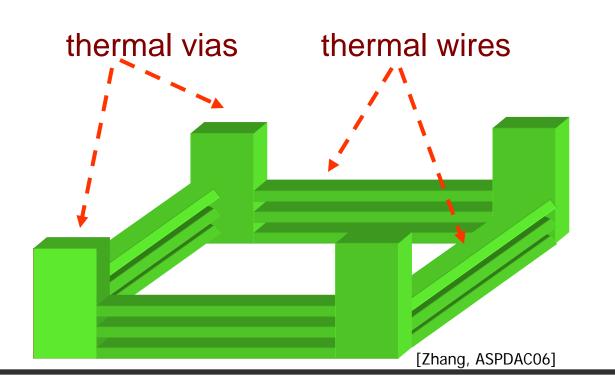
Thermal via insertion



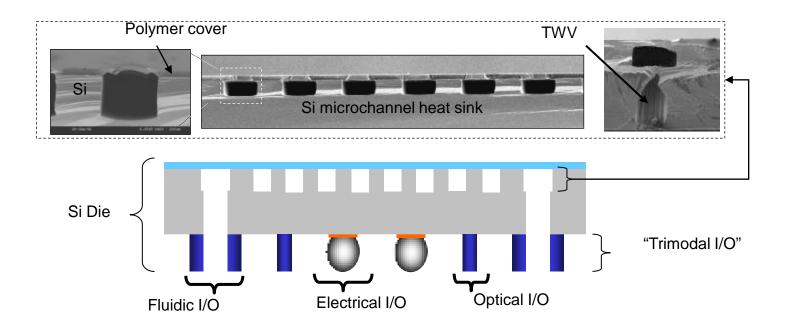
3D routing with integrated thermal via insertion

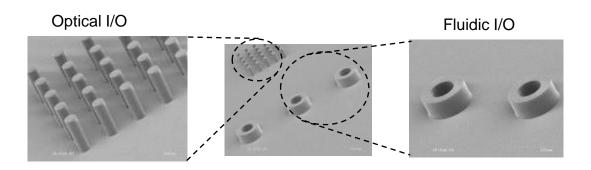
- Build good heat conduction path through dielectric:
 - Thermal vias: interlayers vias dedicated to thermal conduction.
 - Thermal wires: metal wires improves lateral heat conduction.
 - Thermal vias + thermal wires = a thermal conduction network.

- Thermal wires compete with lateral signal wire routing.
- Thermal vias: large, can block lateral signal routing capacity.

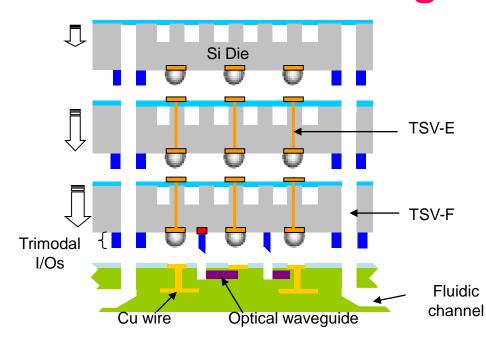


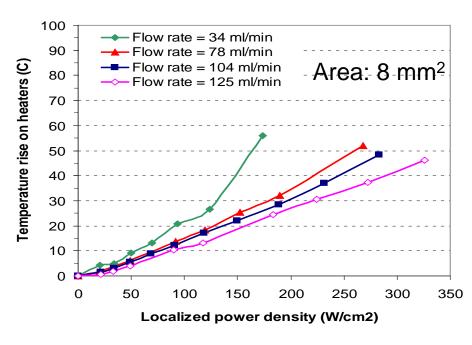
Active cooling techniques





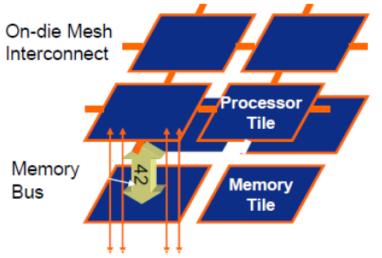
Microfluidic cooling





[Bakir, GaTech] 33

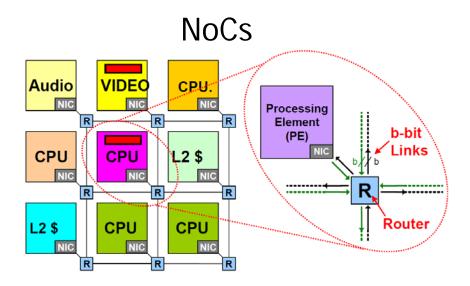
3D and multicore systems



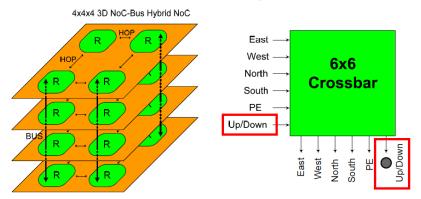
Signals and power from package, through memory, to the processor tile

TSV Pitch	190µm
SRAM die size	275mm ²
SRAM size	256KB per tile, 20MB total
SRAM Power	7W SRAM + 2.2W IO
Bandwidth	12GB/sec/tile, ~1TB/sec total

[Karnik, Intel]



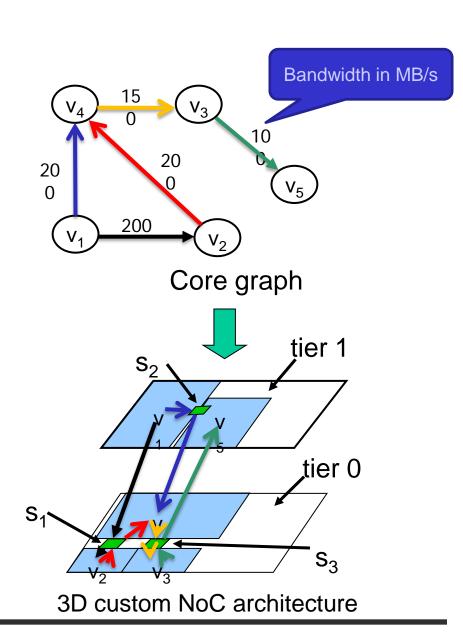
3D bus/NoC hybrid



[Xie, Penn State]

3D NoCs

- Need to build custom NoCs for 3D architectures
- Floorplanning + NoC design
- 3D-specific challenges
 - Technology constraints, like TSV#
 - Tier assignment
 - Placement of switches
 - Accurate power and delay modeling



Conclusion

- Numerous challenging problems in 3D IC design
- Significant research already in floorplanning, placement, routing
- New challenges in architectural-level issues, NoCs, power delivery, test

